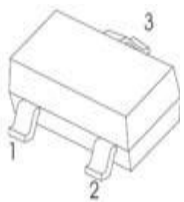
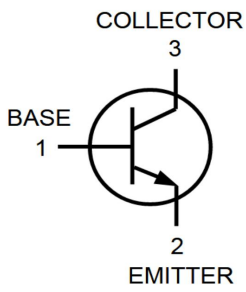
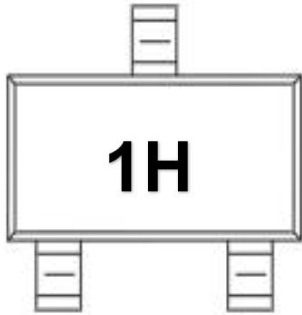
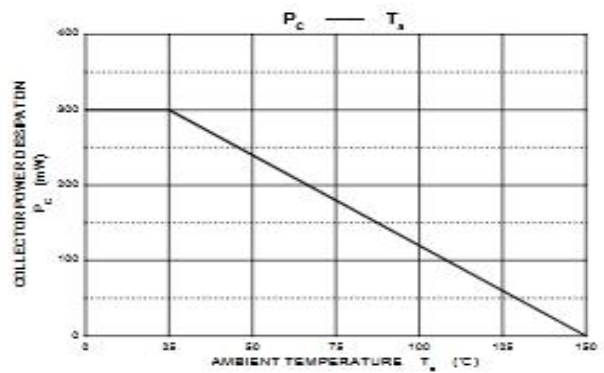
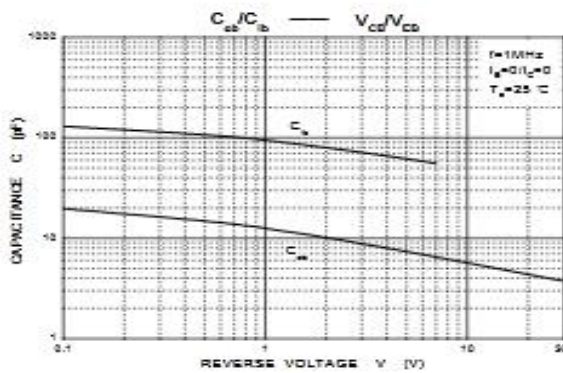
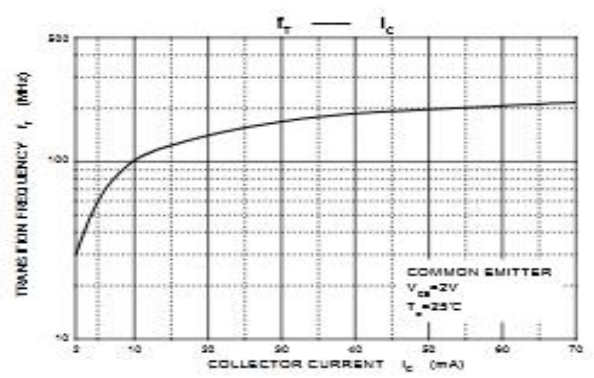
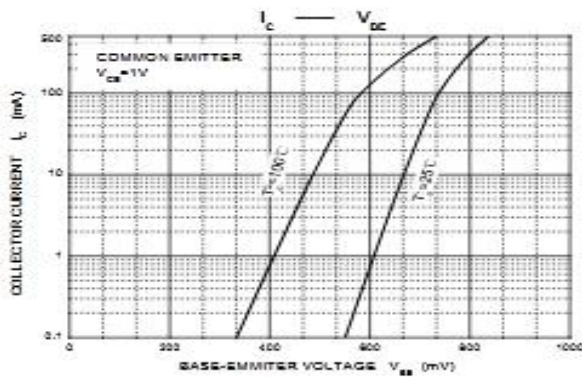
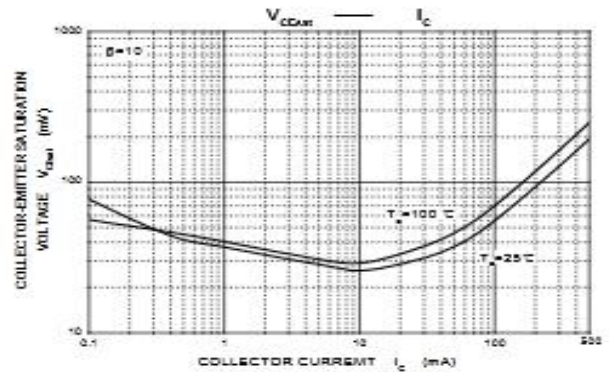
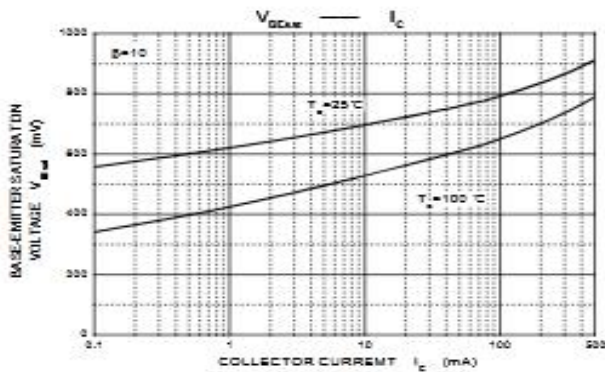
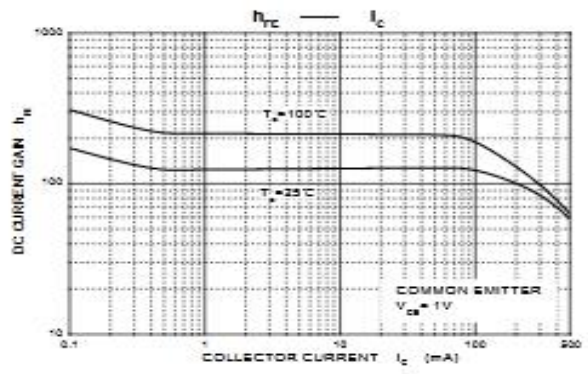
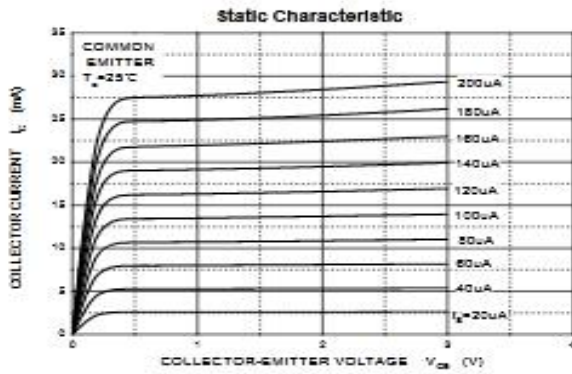


| TRANSISTOR (NPN)  |        | SOT-23 Plastic-Encapsulate Transistors  |      |
|---|--------|---|------|
| <p><u>SOT-23</u></p>  <p>1.BASE<br/>2.EMITTER<br/>3.COLLECTOR</p> <p><b>Equivalent Circuit:</b></p>  |        | <p>Features</p> <p>※ Driver transistor</p> <p><b>MARKING:</b></p>  |      |
| <p><b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b></p>  |        |   |      |
| Parameter   | Symbol | Value   | Unit |
| Collector-Base Voltage  | VCBO   | 60  | V    |
| Collector-Emitter Voltage   | VCEO   | 60  | V    |
| Emitter-Base Voltage  | VEBO   | 4   | V    |
| Collector Current   | IC     | 500   | mA   |
| Collector Power Dissipation   | PC     | 300   | mW   |
| Thermal Resistance From Junction To Ambient   | ROJA   | 417   | °C/W |
| Junction Temperature  | Tj     | 150   | °C   |
| Storage Temperature   | Tstg   | -55~+150  | °C   |

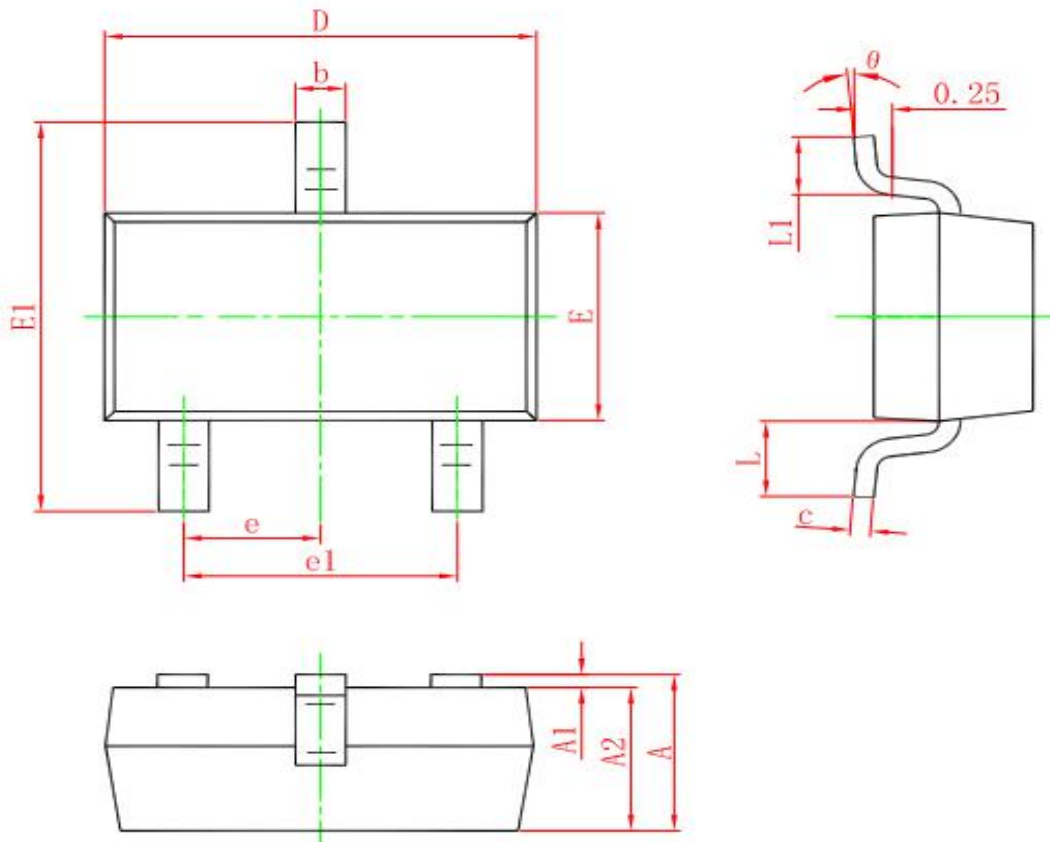
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

| Parameter                            | Symbol          | Test Condition               | Min | Typ | Max  | Unit |
|--------------------------------------|-----------------|------------------------------|-----|-----|------|------|
| Collector-base breakdown voltage     | <b>V(BR)CBO</b> | IC= 100µA, IE=0              | 60  |     |      | V    |
| Collector-emitter breakdown voltage  | <b>V(BR)CEO</b> | IC= 1mA, IB=0                | 60  |     |      | V    |
| Emitter-base breakdown voltage       | <b>V(BR)EBO</b> | IE=100µA, IC=0               | 4   |     |      | V    |
| Collector cut-off current            | <b>ICBO</b>     | VCB=60 V , IE=0              |     |     | 0.1  | µA   |
| Collector cut-off current            | <b>ICEO</b>     | VCB=60V , IE=0               |     |     | 0.1  | µA   |
| Emitter cut-off current              | <b>IEBO</b>     | VEB= 3V , IC=0               |     |     | 0.1  | µA   |
| DC current gain                      | <b>hFE</b>      | VCE=1V, IC= 10mA             | 100 |     | 400  |      |
|                                      | <b>hFE</b>      | VCE=1V, IC= 100mA            | 100 |     |      |      |
| Collector-emitter saturation voltage | <b>VCE(sat)</b> | IC=100 mA, IB= 10mA          |     |     | 0.25 | V    |
| Base-emitter saturation voltage      | <b>VBE(sat)</b> | IC=100 mA, IB= 10mA          |     |     | 1.2  | V    |
| Transition frequency                 | <b>fT</b>       | VCE=2V, IC= 10mA<br>f=100MHz | 100 |     |      | MHz  |

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



**SOT-23 PACKAGE OUTLINE DIMENSIONS**



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min.                      | Max.  | Min.                 | Max.  |
| A      | 0.900                     | 1.150 | 0.035                | 0.045 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041 |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |
| c      | 0.080                     | 0.150 | 0.003                | 0.006 |
| D      | 2.800                     | 3.000 | 0.110                | 0.118 |
| E      | 1.200                     | 1.400 | 0.047                | 0.055 |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100 |
| e      | 0.950 TYP.                |       | 0.037 TYP.           |       |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |
| L      | 0.550 REF.                |       | 0.022 REF.           |       |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)